

AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

In the claims

Claim 1 (currently amended): A method for manufacturing a semiconductor laser device, comprising the steps of:

forming ~~an electrode pattern~~ patterns arranged in a plurality of rows extending in a first direction on an upper surface of a semiconductor wafer ~~stacked~~ having at least a light emission layer, the electrode patterns having opposed two edges extending in the first direction;

cutting the resultant semiconductor wafer for predetermined width to yield a plurality of semiconductor bars; and

sectioning the semiconductor bars ~~into a~~ in desired size ~~sizes~~ to form semiconductor laser devices each having a pair of cleavage surfaces, ~~which are the surfaces being~~ parallel to a ~~chip-width~~ second direction and distant from each other by a ~~predetermined~~ resonator length,

wherein the formed electrode ~~pattern~~ patterns ~~formed in the step of forming an electrode pattern is~~ are continuous at least with each other in a ~~resonator length~~ the first direction, each electrode pattern including a series of markers having a periodical pattern, the markers being formed at one or both of the edges of the electrode patterns, and a minimum unit of the periodical pattern has an overall length in the first direction equal to L/n and not reater than the resonator length, wherein L is the resonator length and n is a positive real number not smaller than one, the first direction being a direction along the resonator length, the second direction being perpendicular to the first direction.

Claims 2-4 (cancelled)

Claim 5 (original): A semiconductor laser device, comprising:

a semiconductor layer portion ~~which includes~~ including at least a light emission layer and has a pair of cleavage surfaces ~~which are~~ the surfaces being parallel to a chip-width direction and distant from each other by a ~~predetermined~~ resonator length; and

an electrode pattern piece formed on an upper surface of the semiconductor layer portion, the electrode pattern piece having opposed two first edges extending in a first direction and opposed two second edges extending in a second direction along the pair of cleavage surfaces,

wherein the two second edges come ~~electrode pattern piece comes~~ in contact with the pair of cleavage ~~planes~~ surfaces ~~at both of the edges of the electrode pattern piece extending in a chip-width direction,~~ each electrode pattern piece including a series of markers having a periodical pattern formed at one or both of the first edges, a minimum unit of the periodical pattern having an overall length in the resonator-length direction equal to L/n and not greater than a resonator length, wherein L is the resonator length and n is a positive real number not smaller than one, the first direction being a direction along the resonator length, wherein the markers can be used to form laser chips of different resonator lengths.

Claims 6-9 (cancelled)

Claim 10 (currently amended): The device of claim 5 ~~claims 6 or 9~~, wherein the series of markers ~~marker is set~~ are arranged so that the ratio of its the overall length of the semiconductor laser device in the resonator-length direction to its maximum length in the chip-width direction is 1:5 to 5:1.

Claim 11. (New): The method of claim 1, wherein the semiconductor wafer is cut in predetermined widths to yield a plurality of semiconductor bars extending in the resonator-length direction, and the plurality of semiconductor bars are cut in predetermined resonator lengths.

Claim 12. (New): The method of claim 11, wherein one of the semiconductor bars is cut in different resonator lengths to yield a plurality of different semiconductor laser devices.

Claim 13. (New): The method of claim 11, wherein one of the semiconductor bars is cut in integral multiple lengths of the overall length of the marker.

Claim 14. (New): The method of claim 5, wherein the series of markers are shaped like teeth of a saw.

Claim 15. (New): The method of claim 5, wherein one of the markers is formed in a shape of right triangle, equilateral triangle, isosceles triangle, semicircle or semiellipse.